

July 28, 2004

Fax No. 703-746-4641

Dale Olson
Patent Publication
United States Patent Office

Re: Docket # 303.678US4 – **Micron Ref. No. 99-1065.03**
U.S. Patent Application Serial Number 09/943,393
Title: STRUCTURE AND METHOD FOR DUAL GATE OXIDE THICKNESS

Dear Mr. Olson:

Pursuant to your phone conversation of last week, I am faxing a copy of the 1449, listing the Fujiwara, M. et al. reference. The complete citation is as follows:

Fujiwara, M., et al., "New Optimization Guidelines for Sub-0.1 micrometer CMOS Technologies with 2 nm NO Gate Oxy-nitrides", 1999 Symposium on VLSI Technology Digest of Technical Papers, pp. 121-122 (1999)

If you need any additional information or documentation, please do not hesitate to contact me.

Very truly yours,

James E. Kanyusik
IDS Specialist

JEK:jk
Enclosure - (1449 - Sheet 1 of 2)